



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
20V	$3.0 \text{m}\Omega$ @ V_{GS} = 4.5V	240mA
	6.0mΩ @ V _{GS} = 1.8V	170mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance:
 - 3.0 Ω @ 4.5V
 - 4.0 Ω @ 2.5V
 - 6.0 Ω @ 1.8V
 - 10 Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.05V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- ESD Protected Gate (HBM 300V)
- Lead, Halogen, and Antimony Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

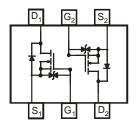
Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)





Top View



Top View Schematic and Transistor Diagram

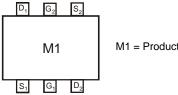
Ordering Information (Note 3)

Part Number	Case	Packaging
DMN26D0UDJ-7	SOT-963	10,000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information (Note 4)



M1 = Product Type Marking Code

Notes: 4. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	240 190	mA
Continuous Drain Current (Note 5) V _{GS} = 1.8V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	180 140	mA
Pulsed Drain Current - T _P = 10µs			I _{DM}	805	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	409	°C/W
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 100 \mu A$	
Zero Gate Voltage Drain Current @ T _C = 25°C	I _{DSS}	_	_	500	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	loos	_		±1	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
, ,	I _{GSS}			±100	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.45	0.8	1.05	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			1.8	3.0	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
			2.5	4.0		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	3.4	6.0		$V_{GS} = 1.8V, I_D = 20mA$	
	,	_	4.7	10.0		$V_{GS} = 1.5V, I_D = 10mA$	
		_	9.5	_		$V_{GS} = 1.2V, I_D = 1mA$	
Forward Transconductance	Y _{fs}	180	240	_	mS	$V_{DS} = 10V, I_D = 0.1A$	
Source-Drain Diode Forward Voltage	V_{SD}	0.5	8.0	1.0	V	$V_{GS} = 0V, I_{S} = 10mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		14.1		pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss		2.9		pF		
Reverse Transfer Capacitance	Crss	_	1.6	_	pF		
SWITCHING CHARACTERISTICS, V _{GS} = 4.5V (Note 7)							
Turn-On Delay Time	t _{d(on)}	_	3.8	_			
Rise Time	tr	_	7.9	_]	$V_{GS} = 4.5V, V_{DD} = 10V$	
Turn-Off Delay Time	t _{d(off)}	_	13.4	_	$I_D = 200 \text{mA}, R_G = 2.0 \Omega$		
Fall Time	t _f	_	15.2	_	1		

- 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch with minimum recommended pad layout; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

 6. Short duration pulse test used to minimize self-heating effect.

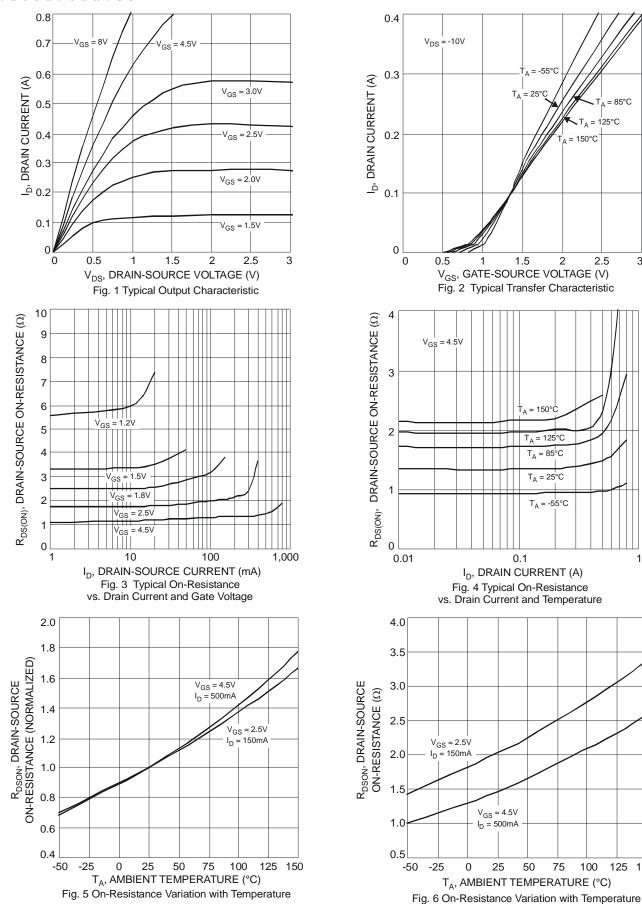
 7. Switching characteristics are independent of operating junction temperature. Guaranteed by design, not subject to production testing.

125°C

2.5

3







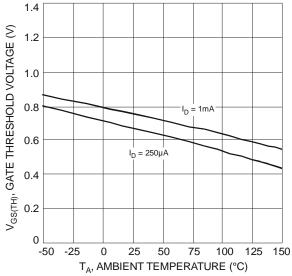
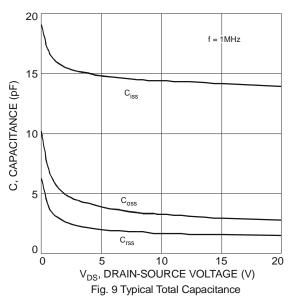
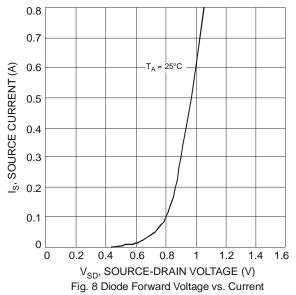


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





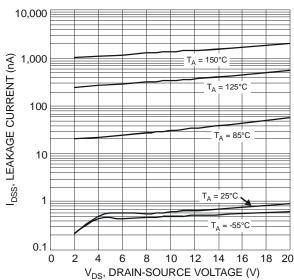
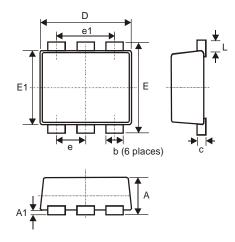


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

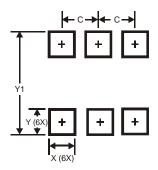
Package Outline Dimensions



SOT-963				
Dim	Min	Max	Тур	
Α	0.40	0.50	0.45	
A1	0	0.05	-	
С	0.120	0.180	0.150	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
E1	0.75	0.85	0.80	
L	0.05	0.15	0.10	
b	0.10	0.20	0.15	
е	0.35 Typ			
e1	0.70 Typ			
All	All Dimensions in mm			



Suggested Pad Layout



Dimensions	Value (in mm)
С	0.350
Х	0.200
Y	0.200
Y1	1.100

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